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**ABSTRACT OF THE DISCLOSURE**

The semiconductor device comprises a semiconductor substrate 10, a conducting film 20 formed on the semiconductor substrate 10 and including two conductor patterns adjacent to each other; an etching stopper film covering the upper surface of the conducting film 20; an insulation film 28 which includes a contact hole which reaches the semiconductor substrate 10 between the two conductor patterns and the an end of which is positioned on the etching stopper film 22 on the two conductor patterns; and a sidewall insulation film 32 formed on the side walls of the conducting film 20 and of the etching stopper film 22 in the contact hole. The fluctuation of a contact hole size due to disalignment of the lithography can be restrained, and in the lithography step of opening the contact hole, the photoresist can have a large openings size, which facilitate the lithography step.